

Wafer Bonding

Elements of Interest Up to 150mm	Process Temperature 350°C	Bonding Agent Cyclotene 3022™
Chamber Configuration Single	Temperature Ramp Controlled at 6°/min up/down	Temperature Control Resistant and IR heating and water cooling

Benefits

- Almost any flat substrates can be bonded to each other, including silicon, GaAs, InP, glass, quartz, ceramics, aluminum and other metals.
- Wafers with thin film, such as oxides, metals, nitrides and others, can also be bonded

Typical Application

Adhesive bonding for typical substrate-to-substrate designs

Although all statements and information presented in this document are believed to be accurate and reliable, they are presented without warranty or guarantee of any kind, express or implied. Information presented does not relieve the end user from carrying out their own tests to determine suitability for use in their application. User assumes all risk and liability for product use or information and results obtained. Suggestions for use of material and processes are made without representation or warranty that any such is free from patent infringement and are not recommendations for patent infringement. Please see MSDS for information regarding health and safety of material use.